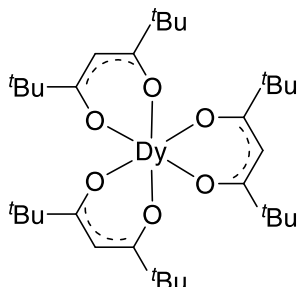


Catalog # 66-8500 Tris(2,2,6,6-tetramethyl-3,5-heptanedionato)dysprosium(III), 98+% (99.9%-Dy) (REO)
[Dy(TMHD)3]



Thermal Behavior:

- Melting point: 182-185°C; 186°C [1]
- Decomposition: 265°C
- TGA data and diagram are available in [1]

Technical Notes:

1. Precursor and dopant used for dysprosium thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
Dy ₂ O ₃	ALD	125°C	1.5-2.3 Torr	O ₃	300°C	2, 3
DyScO ₃	ALD	125-128°C	1.5-2.3 Torr	Sc(thd) ₃ ; O ₃	300°C	4
	ALD	150°C	-	Sc(thd) ₃ ; O ₃	300-390°C	5
Dy:Al ₂ O ₃	CVD	135°C	165 Torr	Al(acac) ₃ ;	850-1120°C	6
Dy:SiC _x O _y	CVD	180°C	-	MeSiH ₃	600°C	7
DyZr _x O _y	ALD	160°C	~2 Torr	ZrCl ₄ , H ₂ O	300°C	8
DyTi _x O _y	ALD	140°C	1.7 Torr	TiCl ₄ , O ₃ , O ₃ /H ₂ O	250-350°C	9
DyYb _x Ti _y O _z	ALD	130°C	-	Yb(thd) ₃ , TiCl ₄ , O ₃ , H ₂ O	300°C	10

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